

AMENDMENTS

In the Claims:

✓
Please cancel claims 29-36.

Please amend claims 25 and 27 as follows:

D¹

25. (Twice Amended) A semiconductor substrate comprising:
an n-th patterned mask containing a material having a growth suppressing effect,
provided on or above a lower substrate, wherein n is an integer of 1 or more;
an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the
n-th mask;
an (n+1)-th patterned mask containing a material having a growth suppressing material
substantially provided above an opening of the n-th patterned mask; and an (n+1)-th nitride
semiconductor crystal layer grown on or above the lower substrate via the (n+1)-th patterned
mask,
wherein the n-th patterned mask and the (n+1)-th patterned mask are respectively
patterned in a stripe shape, and a direction of the stripe of the n-th patterned mask is twisted from
a direction of the stripe of the (n+1)-th patterned mask.

D²

27. (Amended) A semiconductor substrate comprising:
an n-th patterned mask containing a material having a growth suppressing effect,
provided on or above a lower substrate, wherein n is an integer of 1 or more;
an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the
n-th mask;

D²
an (n+1)-th patterned mask containing a material having a growth suppressing effect, provided so as to be at an angle of about 90° or 120° relative to the n-th patterned mask; and an (n+1)-th nitride semiconductor crystal layer grown on or above the lower substrate via the (n+1)-th patterned mask.

Please add new claims 37-58 as follows:

D³
37. (New) A semiconductor substrate comprising:
an n-th patterned mask containing a material having a growth suppressing effect, provided on or above a lower substrate, wherein n is an integer of 1 or more;
an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the n-th mask;
an (n+1)-th patterned mask containing a material having a growth suppressing material substantially provided above an opening of the n-th patterned mask; and an (n+1)-th nitride semiconductor crystal layer grown on or above the lower substrate via the (n+1)-th patterned mask,
wherein the first to (n+1)-th patterned masks are patterned in such a manner that a combination of the first to (n+1)-th patterned masks covers the entire surface of the lower substrate.

38. (New) A light emitting device produced by using the semiconductor substrate of claim 37.

39. (New) A semiconductor substrate according to claim 25, wherein a width of the stripe of the (n+1)-th patterned mask is equal to or larger than a width of the stripe of the n-th patterned mask.

40. (New) A semiconductor substrate according to claim 27, wherein a width of the stripe of the (n+1)-th patterned mask is equal to or larger than a width of the stripe of the n-th patterned mask.

41. (New) A semiconductor substrate according to claim 37, wherein a width of the stripe of the (n+1)-th patterned mask is equal to or larger than a width of the stripe of the n-th patterned mask.

42. (New) A semiconductor substrate according to claim 25, wherein the n-th nitride semiconductor crystal layer is made of AlGaN or InGaN.

43. (New) A semiconductor substrate according to claim 27, wherein the n-th nitride semiconductor crystal layer is made of AlGaN or InGaN.

44. (New) A semiconductor substrate according to claim 37, wherein the n-th nitride semiconductor crystal layer is made of AlGaN or InGaN.

45. (New) A semiconductor substrate according to claim 25, wherein a stripe width of the second mask is smaller than each opening of the first mask.

46. (New) A semiconductor substrate according to claim 27, wherein a stripe width of the second mask is smaller than each opening of the first mask.

47. (New) A semiconductor substrate according to claim 37, wherein a stripe width of the second mask is smaller than each opening of the first mask.

48. (New) A semiconductor substrate according to claim 25, wherein the n-th, and (n+1)-th are formed of the same material.

49. (New) A semiconductor substrate according to claim 27, wherein the n-th, and (n+1)-th are formed of the same material.

50. (New) A semiconductor substrate according to claim 37, wherein the n-th, and (n+1)-th are formed of the same material.

51. (New) A semiconductor substrate according to claim 25, wherein the thickness of the n-th and (n+1)-th masks are the same as each other.

52. (New) A semiconductor substrate according to claim 27, wherein the thickness of the n-th and (n+1)-th masks are the same as each other.

53. (New) A semiconductor substrate according to claim 37, wherein the thickness of the n-th and (n+1)-th masks are the same as each other.

54. (New) A semiconductor substrate according to claim 25, wherein the lower substrate is GaN.

55. (New) A semiconductor substrate according to claim 27, wherein the lower substrate is GaN.

56. (New) A semiconductor substrate according to claim 37, wherein the lower substrate is GaN.

D3
Sub 1
57. (New) A semiconductor substrate comprising:
an n-th patterned mask containing a material having a growth suppressing effect,
provided on or above a lower substrate, wherein n is an integer of 1 or more;
an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the
n-th mask;
an (n+1)-th patterned mask containing a material having a growth suppressing material
substantially provided above an opening of the n-th patterned mask; and an (n+1)-th nitride
semiconductor crystal layer grown on or above the lower substrate via the (n+1)-th patterned
mask,
wherein the n-th patterned mask and the (n+1)-th patterned mask are respectively
patterned in a stripe shape.

58. (New) A semiconductor substrate comprising:
an n-th patterned mask containing a material having a growth suppressing effect,
provided on or above a lower substrate, wherein n is an integer of 1 or more;
an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the
n-th mask;

D³ an (n+1)-th patterned mask containing a material having a growth suppressing effect,
provided so as to be at an angle of about 90° or more relative to the n-th patterned mask; and
an (n+1)-th nitride semiconductor crystal layer grown on or above the lower substrate via
the (n+1)-th patterned mask.
